# ACTT6X-800E



# AC Thyristor Triac power switch Rev. 1 — 26 October 2011

Product data sheet

#### **Product profile** 1.

### 1.1 General description

Planar passivated AC Thyristor Triac power switch in a SOT186A (TO-220F) "full pack" plastic package with self-protective capabilities against low and high energy transients.

### 1.2 Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- Direct interfacing with low power drivers and microcontrollers
- Full cycle AC conduction
- Isolated mounting base package
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs

- Planar passivated for voltage ruggedness and reliability
- Safe clamping capability for low energy over-voltage transients
- Self-protective turn-on during high energy voltage transients
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

### 1.3 Applications

- AC Fan controllers
- Highly inductive, resistive and safety loads of lower power
- Large and small appliances (White Goods)
- Loads such as contactors, circuit breakers, valves, dispensers and door locks
- Pump motor circuits
- Reversing induction motor control

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; see Figure 5; see Figure 6	-	-	51	Α



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 81 ^{\circ}\text{C}$ ; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 4</u>	-	-	6	Α
V <sub>CL</sub>	clamping voltage	$I_{CL} = 0.1 \text{ mA}; t_p = 1 \text{ ms}; T_j = 25 \text{ °C}$	850	-	-	V
$V_{PP}$	peak pulse voltage	$T_j = 25$ °C; non-repetitive, off-state; see Figure 3	-	-	2	kV

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	CM	common		10
2	LD	load	mb	LD
3	G	gate		G—
mb	n.c.	mounting base; isolated		 CM 003aaf29t
			SOT186A (TO-220F)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
ACTT6X-800E	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 81$ °C; see Figure 1; see Figure 2; see Figure 4	-	6	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	56	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; see Figure 5; see Figure 6	-	51	Α
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	13	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 9 \text{ A}$ ; $I_G = 0.2 \text{ A}$ ; $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-	100	A/µs
I <sub>GM</sub>	peak gate current	t = 20 μs	-	2	Α
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C
V <sub>PP</sub>	peak pulse voltage	T <sub>j</sub> = 25 °C; non-repetitive, off-state; see Figure 3	-	2	kV

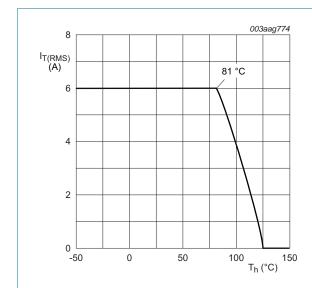
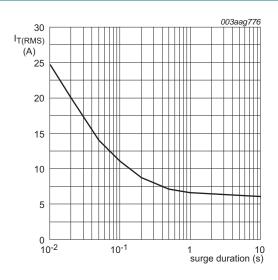


Fig 1. RMS on-state current as a function of heatsink temperature; maximum values



 $f = 50 \text{ Hz}; T_h = 81 \,^{\circ}\text{C}$ 

Fig 2. RMS on-state current as a function of surge duration; maximum values

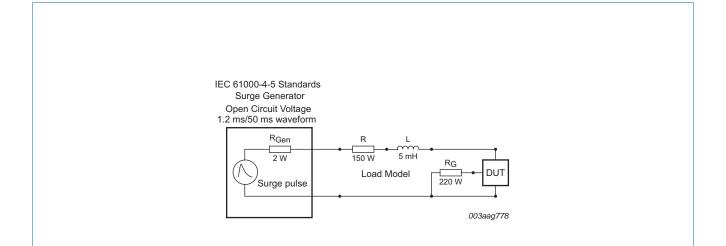


Fig 3. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

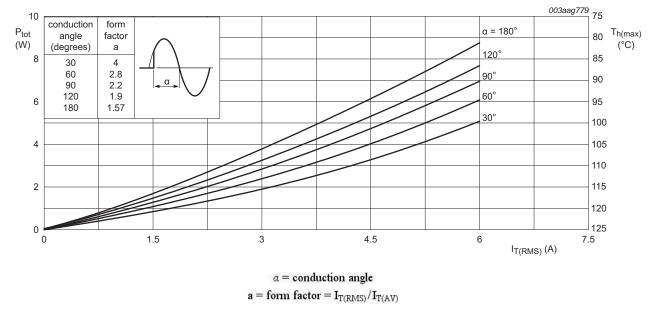


Fig 4. Total power dissipation as a function of RMS on-state current; maximum values

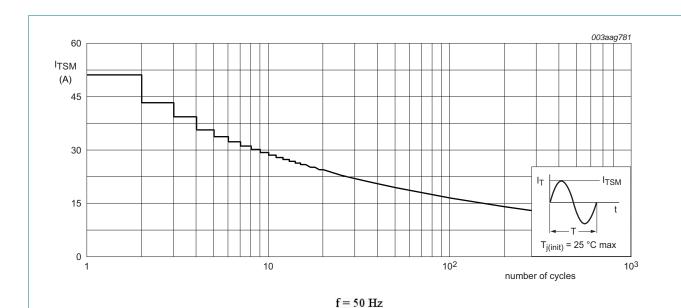


Fig 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

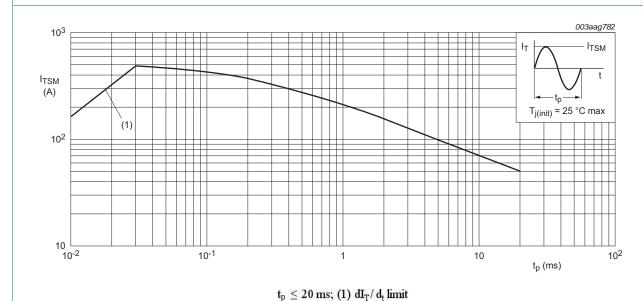
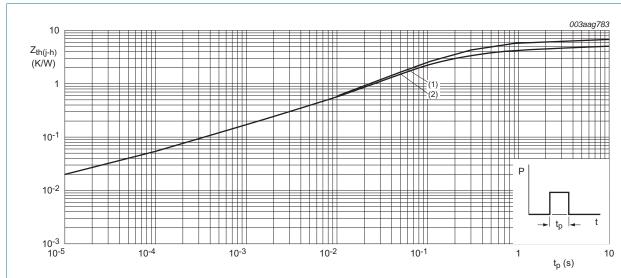


Fig 6. Non-repetitive peak on-state current as a function of pulse width; maximum values

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full or half cycle with heatsink compound; see Figure 7	-	-	5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	55	-	K/W



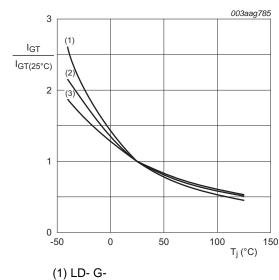
- (1) full or half cycle without heatsink compound
- (2) full or half cycle with heatsink compound

Fig 7. Transient thermal impedance from junction to heatsink as a function of pulse width

## 6. Characteristics

Table 6. Characteristics

	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G+;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 8}}{}$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 8}}{}$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; LD- G-;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	-	10	mA
IL	latching current	$V_D = 12 \text{ V; } I_G = 100 \text{ mA; LD+ G+;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or } 100 \text{ mA; LD+ G+;}}$	-	-	30	mA
		$V_D = 12 \text{ V; } I_G = 100 \text{ mA; LD+ G-;}$ $T_j = 25 ^{\circ}\text{C; see } \frac{\text{Figure 9}}{\text{C}}$	-	-	40	mA
		$V_D = 12 \text{ V; } I_G = 100 \text{ mA; LD- G-;}$ $T_j = 25 ^{\circ}\text{C; see } \frac{\text{Figure 9}}{\text{C}}$	-	-	30	mA
I <sub>H</sub>	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{\text{ Figure } 10}$	-	-	25	mΑ
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 8 A; see <u>Figure 11</u>	-	-	1.7	V
$V_{GT}$	gate trigger voltage	$V_D = 400 \text{ V}; I_T = 100 \text{ mA}; T_j = 125 ^{\circ}\text{C};$ see Figure 12	0.2	-	-	V
		$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; T_j = 25 \text{ °C};$ see Figure 12	-	-	1.5	V
I <sub>D</sub>	off-state current	$V_D = 800 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	10	μΑ
		$V_D = 800 \text{ V}; T_j = 125 \text{ °C}$	-	-	0.5	mΑ
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; gate open circuit; exponential waveform; see Figure 13	500	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 6 A; $dV_{com}/dt$ = 20 V/ $\mu$ s; (snubberless condition); gate open circuit; see <u>Figure 14</u> ; see <u>Figure 15</u>	3.5	-	-	A/ms
		$V_D = 400 \text{ V; } T_j = 125 \text{ °C; } I_{T(RMS)} = 6 \text{ A;}$ $dV_{com}/dt = 10 \text{ V/}\mu\text{s; gate open circuit;}$ $see \underline{Figure 14}$ ; $see \underline{Figure 15}$	5	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 6 \text{ A};$ $dV_{com}/dt = 1 \text{ V/}\mu\text{s};$ gate open circuit; see <u>Figure 14</u> ; see <u>Figure 15</u>	10	-	-	A/ms
	clamping voltage	$I_{CL} = 0.1 \text{ mA}; t_p = 1 \text{ ms}; T_i = 25 \text{ °C}$	850			V



- (2) LD+ G+
- (3) LD+ G-

Fig 8. Normalized gate trigger current as a function of junction temperature

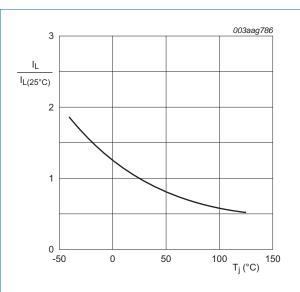


Fig 9. Normalized latching current as a function of junction temperature

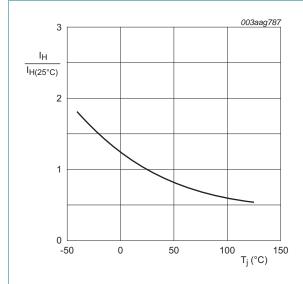
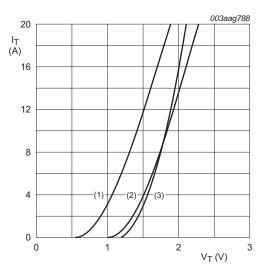


Fig 10. Normalized holding current as a function of junction temperature



 $V_o = 1.109 \text{ V}; R_s = 0.076 \Omega$ 

(1) T<sub>i</sub> = 125 °C; typical values

(2) T<sub>i</sub> = 125 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig 11. On-state current as a function of on-state voltage

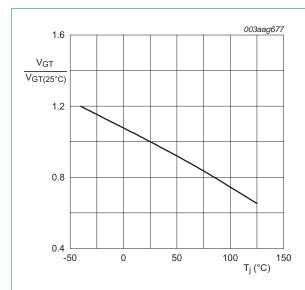
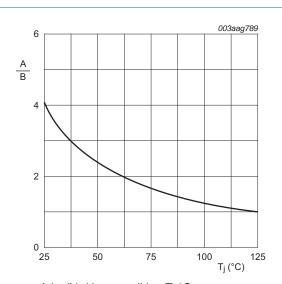
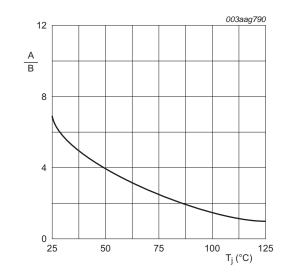


Fig 12. Normalized gate trigger voltage as a function of junction temperature



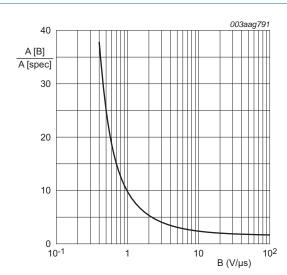
A is  $dV_D/dt$  at condition  $T_j$  °C B is  $dV_D/dt$  at condition  $T_j$  125 °C

Fig 13. Normalized rate of rise of off-state voltage as a function of junction temperature



A is  $dl_{com}/dt$  at condition  $T_j$  °C B is  $dl_{com}/dt$  at condition  $T_j$  125 °C  $V_D = 400 \text{ V}$ 

Fig 14. Normalized critical rate of rise of commutating current as a function of junction temperature



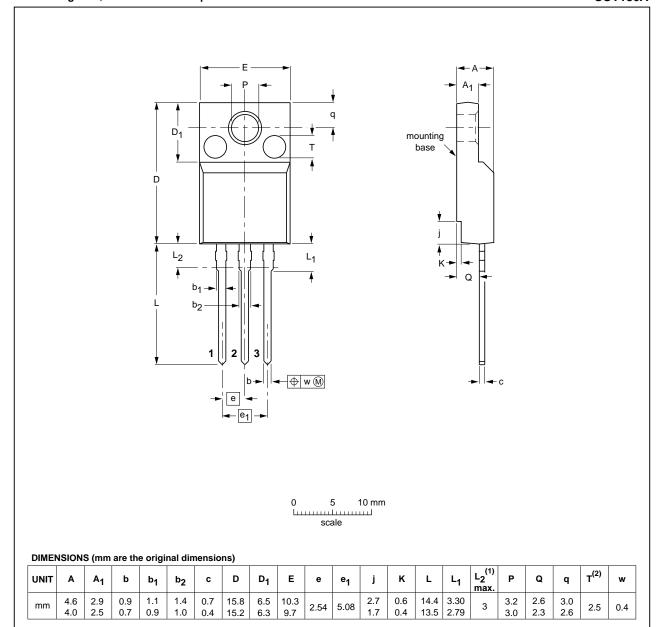
A[B] is  $dI_{com}/dt$  at condition B,  $dV_{com}/dt$ A[spec] is the specified data sheet value of  $dI_{com}/dt$ turn-off time < 20 ms

Fig 15. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values

## 7. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



#### Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are  $\varnothing$  2.5  $\times$  0.8 max. depth

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT186A		3-lead TO-220F			<del>-02-04-09</del> 06-02-14	

Fig 16. Package outline SOT186A (TO-220F)

ACTT6X-800E



# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
ACTT6X-800E v.1	20111026	Product data sheet	-	-

### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# ACTT6X-800E

### **AC Thyristor Triac power switch**

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